

## Low voltage fast-switching NPN power transistor

### Features

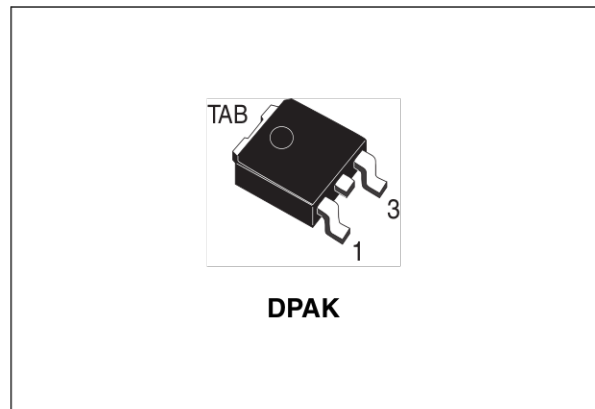
- Very low collector to emitter saturation voltage
- High current gain characteristic
- Fast-switching speed

### Applications

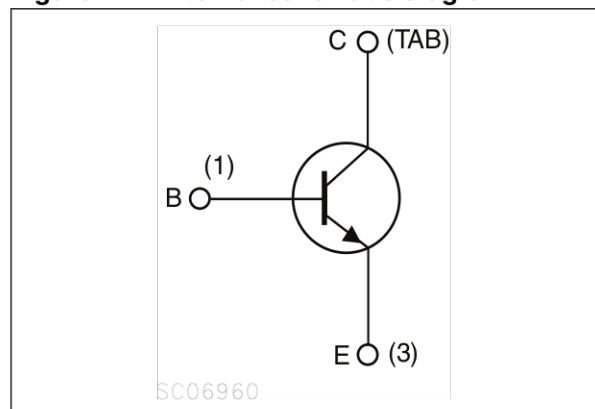
- Voltage regulators
- High efficiency low voltage switching applications

### Description

The device is a low voltage NPN transistor with exceptional high gain performance coupled with very low saturation voltage. It is designed in planar technology with "base island" layout.



**Figure 1. Internal schematic diagram**



**Table 1. Device summary**

Order code	Marking	Packages	Packaging
2STD1665T4	D1665	DPAK	Tape and reel

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	150	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	65	V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	7	V
$I_C$	Collector current	6	A
$I_{CM}$	Collector peak current ( $t_P < 5\text{ms}$ )	20	A
$I_B$	Base current	1	A
$P_{tot}$	Total dissipation at $T_a = 25\text{ °C}$	15	W
$T_{stg}$	Storage temperature	-65 to 150	°C
$T_J$	Max. operating junction temperature	150	°C

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-a}^{(1)}$	Thermal resistance junction-ambient	8.33 max	°C/W

1. Device mounted on a PCB area of  $1\text{ cm}^2$

## 2 Electrical characteristics

( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise specified).

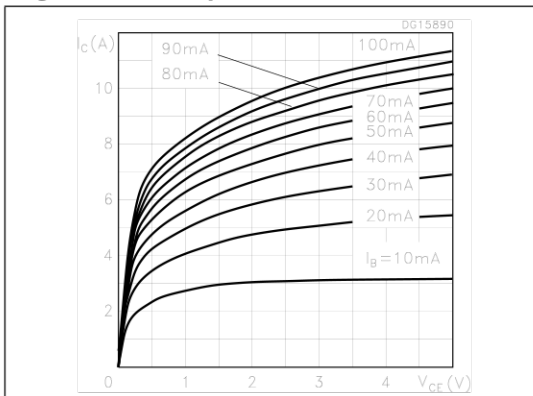
**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CBO}}$	Collector cut-off current ( $I_{\text{E}} = 0$ )	$V_{\text{CB}} = 120 \text{ V}$ $V_{\text{CB}} = 120 \text{ V} \quad T_{\text{C}} = 100^{\circ}\text{C}$			50 1	nA $\mu\text{A}$
$I_{\text{EBO}}$	Emitter cut-off current ( $I_{\text{C}} = 0$ )	$V_{\text{EB}} = 7 \text{ V}$			10	nA
$V_{(\text{BR})\text{CBO}}^{(1)}$	Collector-base breakdown voltage ( $I_{\text{E}} = 0$ )	$I_{\text{C}} = 100 \mu\text{A}$	150			V
$V_{(\text{BR})\text{CEO}}^{(1)}$	Collector-emitter breakdown voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = 10 \text{ mA}$	65			V
$V_{(\text{BR})\text{EBO}}^{(1)}$	Emitter-base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = 100 \mu\text{A}$	7			V
$V_{\text{CE}(\text{sat})}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 100 \text{ mA} \quad I_{\text{B}} = 5 \text{ mA}$ $I_{\text{C}} = 1 \text{ A} \quad I_{\text{B}} = 50 \text{ mA}$ $I_{\text{C}} = 2 \text{ A} \quad I_{\text{B}} = 50 \text{ mA}$ $I_{\text{C}} = 6 \text{ A} \quad I_{\text{B}} = 150 \text{ mA}$ $I_{\text{C}} = 6 \text{ A} \quad I_{\text{B}} = 300 \text{ mA}$		50 100 260 230	120 200 600 380	mV mV mV mV
$V_{\text{BE}(\text{sat})}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 4 \text{ A} \quad I_{\text{B}} = 200 \text{ mA}$		1	1.15	V
$V_{\text{BE}(\text{on})}^{(1)}$	Base-emitter on voltage	$I_{\text{C}} = 4 \text{ A} \quad V_{\text{CE}} = 1 \text{ V}$		0.85	1	V
$h_{\text{FE}}$	DC current gain	$I_{\text{C}} = 10 \text{ mA} \quad V_{\text{CE}} = 1 \text{ V}$ $I_{\text{C}} = 2 \text{ A} \quad V_{\text{CE}} = 1 \text{ V}$ $I_{\text{C}} = 5 \text{ A} \quad V_{\text{CE}} = 1 \text{ V}$ $I_{\text{C}} = 10 \text{ A} \quad V_{\text{CE}} = 1 \text{ V}$	150 150 90 30	320 310 175 65	350	
$C_{\text{CBO}}$	Collector-base capacitance ( $I_{\text{E}}=0$ )	$V_{\text{CB}} = 10 \text{ V} \quad f = 1 \text{ MHz}$		45		pF
$t_{\text{on}}$ $t_{\text{s}}$ $t_{\text{f}}$	Resistive load Turn-on time Storage time Fall time	$I_{\text{C}} = 3 \text{ A} \quad V_{\text{CC}} = 10 \text{ V}$ $I_{\text{B}(\text{on})} = -I_{\text{B}(\text{off})} = 300 \text{ mA}$ $V_{\text{BB}(\text{off})} = -5 \text{ V}$		90 800 90		ns ns ns

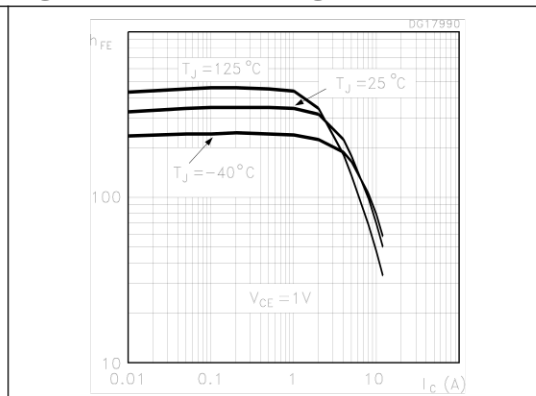
1. Pulse test: pulse duration  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$

## 2.1 Electrical characteristics (curves)

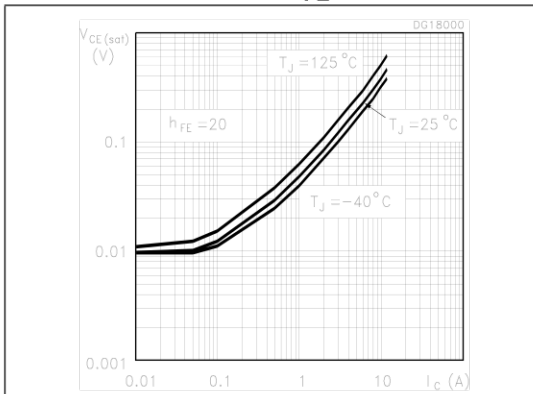
**Figure 2. Output characteristics**



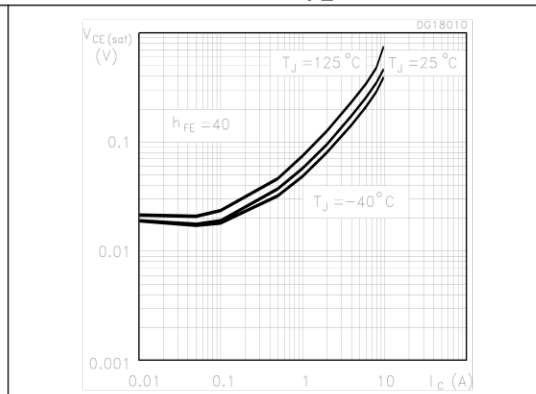
**Figure 3. DC current gain**



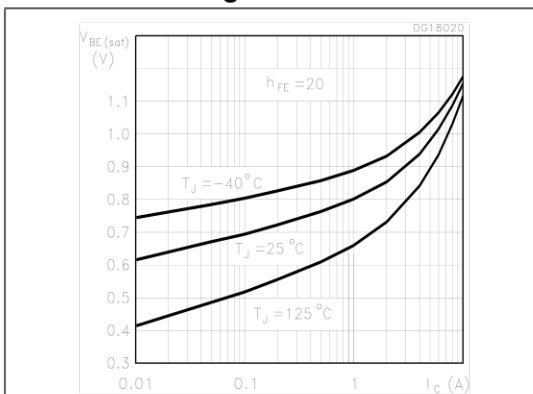
**Figure 4. Collector-emitter saturation voltage - ( $h_{FE} = 20$ )**



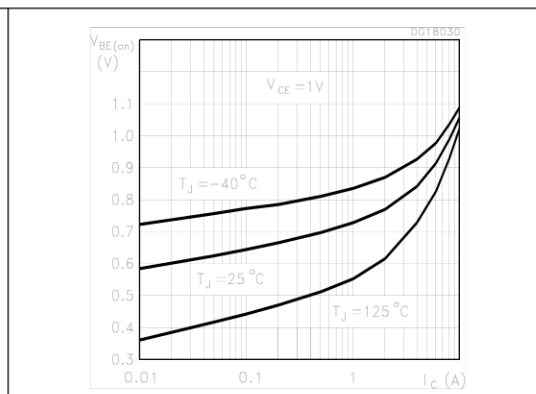
**Figure 5. Collector-emitter saturation voltage - ( $h_{FE} = 40$ )**



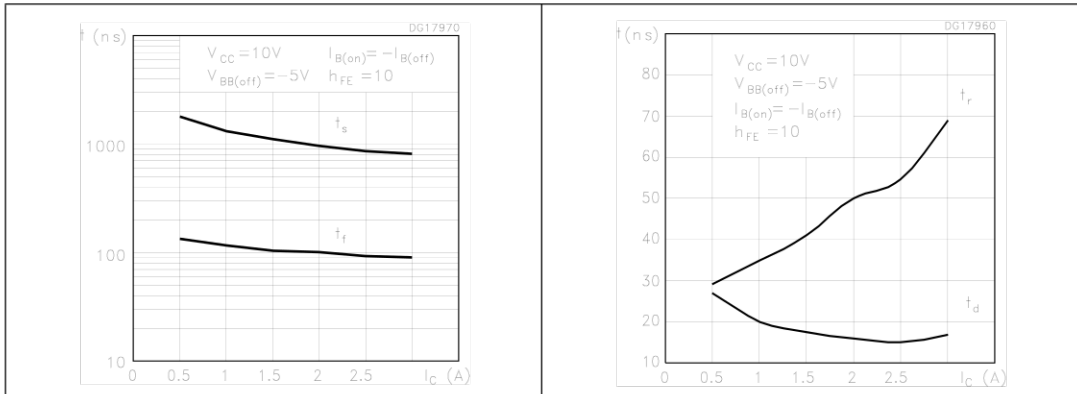
**Figure 6. Base-emitter saturation voltage**



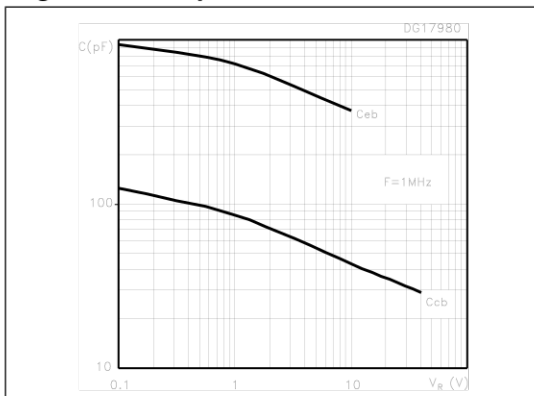
**Figure 7. Base-emitter on voltage**



**Figure 8. Resistive load switching off**      **Figure 9. Resistive load switching on**

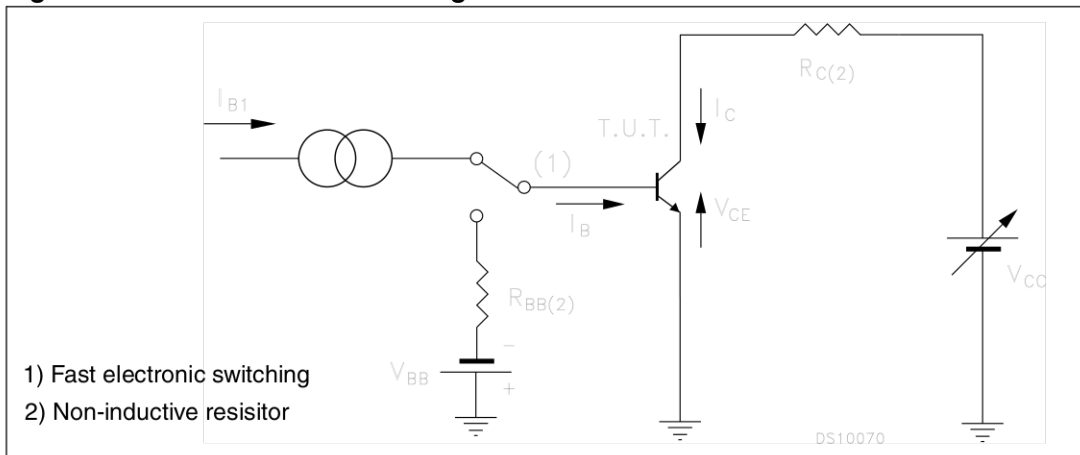


**Figure 10. Capacitance**



## 2.2 Test circuit

**Figure 11. Resistive load switching time**



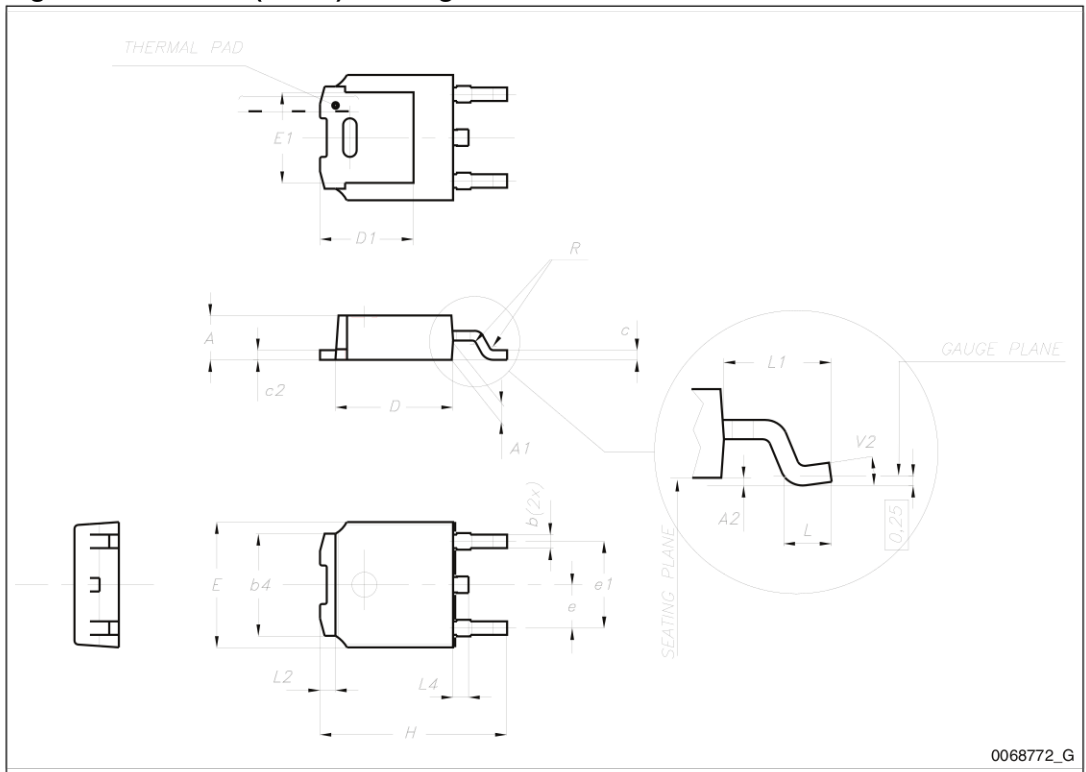
### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 5. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 12. TO-252 (DPAK) drawings





## 4 Revision history

**Table 6. Document revision history**

Date	Revision	Changes
08-May-2006	1	Initial release
27-Mar-2008	2	New graphics
08-Feb-2011	3	Updated <a href="#">Table 2</a> and <a href="#">3</a>

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